Session Program

21–23 Nov 2016

29th RD50 Workshop (CERN)

TCT & Device simulations

CERN, 6/2-024 - BE Auditorium Meyrin
6-2-024

Tuesday 22 November

14:00

TCT & Device simulations

Session | **Location:** CERN, 6/2-024 - BE Auditorium Meyrin, 6-2-024

14:00–14:20 **Physical limits on the inter-strip resistance for planar strip sensors**

Speaker
Vitaliy Fadeyev

14:20–14:40

Calculation of the effective space charge profile of a detector using TRACS

Speaker
Julio Calvo Pinto

14:40–15:00

LGAD design for harsh radiation environments using TCAD simulations.

Speaker
Ashutosh Bhardwaj

15:00–15:20

Simulation of Low Gain Avalanche Detector characteristics based on the concept of negative feedback in irradiated silicon detectors with carrier impact ionization (Part II)

Speaker
Dr Elena Verbitskaya

15:20–15:40

Simulation of Dynamic Characteristics of GaN p-i-n Avalanche Diode Type Particle Detector

Speaker
Juozas Vysniauskas

15:40–16:10 **Coffee Break**

16:10–16:30

TCAD simulations of p-bulk silicon sensors after a large range of fluences

Speaker
Marco Bomben

16:30–16:50 **Fitting the LGAD simulation**

Speaker
Francisco Rogelio Palomo Pinto

16:50–17:10

Insight into the behaviour of futuristic low bulk resistivity Si sensors using device simulation.

17:10–17:30

Validation strategy for the simulation of highly irradiated silicon pixel sensors

Speaker

Joern Schwandt

19:00

17:30–18:00 **Discussion: Device Simulation & RD50 Simulation Working Group**